

The RF Line

NPN Silicon

High-Frequency Transistor

Designed for small-signal amplification at frequencies to 500 MHz. Specifically packaged for use in thick and thin-film circuits using surface mount components.

- High Gain — $G_{pe} = 15$ dB Typ @ $f = 200$ MHz
- Low Noise — $NF = 4.5$ dB Typ @ $f = 200$ MHz
- Available in tape and reel packaging options:
 T1 suffix = 3,000 units per reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	50	mAdc
Maximum Junction Temperature	T_{Jmax}	150	°C
Power Dissipation, $T_{case} = 75^\circ\text{C}$ (1) Derate linearly above $T_{case} = 75^\circ\text{C}$ @	$P_D(max)$	0.375 5.00	W mW/°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Storage Temperature	T_{stg}	-55 to +150	°C
Thermal Resistance Junction to Case	$R_{\theta JC}$	200	°C/W

DEVICE MARKING

MMBR5179LT1 = 7H

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 3.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.001$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.01$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15$ Vdc, $I_E = 0$)	I_{CBO}	—	—	0.02	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 3.0$ mAdc, $V_{CE} = 1.0$ Vdc)	h_{FE}	30	—	250	—
Collector-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{CE(sat)}$	—	—	0.4	Vdc
Base-Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc)	$V_{BE(sat)}$	—	—	1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

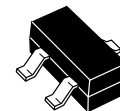
Current-Gain — Bandwidth Product ($I_C = 5.0$ mAdc, $V_{CE} = 6.0$ Vdc, $f = 100$ MHz)	f_T	—	1,400	—	MHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, $f = 0.1$ to 1.0 MHz)	C_{cb}	—	—	1.0	pF
50 ohm Noise Figure ($I_C = 1.5$ mAdc, $V_{CE} = 6.0$ Vdc, $R_S = 50$ Ω , $f = 200$ MHz)	NF	—	4.5	—	dB
Common-Emitter Amplifier Power Gain ($V_{CE} = 6.0$ Vdc, $I_C = 5.0$ mAdc, $f = 200$ MHz)	G_{pe}	—	15	—	dB

NOTE:

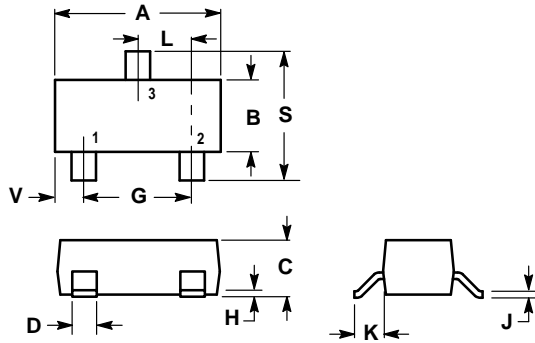
1. Case temperature measured on collector lead immediately adjacent to body of package.

MMBR5179LT1

RF AMPLIFIER
 TRANSISTOR
 NPN SILICON



CASE 318-08, STYLE 6
 SOT-23
 LOW PROFILE
 (TO-236AA/AB)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

**CASE 318-08
ISSUE AF**

Freescale Semiconductor, Inc. ARCHIVE INFORMATION

ARCHIVE INFORMATION

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How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution;
P.O. Box 5405, Denver, Colorado 80217. 1-303-675-2140 or 1-800-441-2447

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141,
4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

Customer Focus Center: 1-800-521-6274

Mfax™: RMFAX0@email.sps.mot.com – TOUCHTONE 1-602-244-6609
Motorola Fax Back System – US & Canada ONLY 1-800-774-1848
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ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

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